



# 제 31회 한국반도체학술대회

The 31st Korean Conference on Semiconductors

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 15:40-17:25

Room G(201), 2층

## K. Memory (Design & Process Technology) 분과

### [FG3-K] NAND Flash Memory

좌장: 강대웅 교수(서울대학교), 김동찬 교수(SK Hynix University)

초청발표 FG3-K-1 15:40-16:10	Next Evolution through the Properties of 3D NAND Flash Dongchan Kim, Jinkook Kim SK hynix
FG3-K-2 16:10-16:25	HfAlO <sub>2</sub> 기반의 이중 메모리 메커니즘을 가지는 V-NAND Flash 소자의 메모리 윈도우 및 열적 안정성 개선 추준홍, 신의중, 강창연, 김승훈, 조병진 한국과학기술원 전기 및 전자공학부
FG3-K-3 16:25-16:40	Quantitative Analysis on Z-interference Using Reprogram Scheme in 3D NAND Flash Memory V <sub>th</sub> Distribution Jooyoung Lee <sup>1</sup> and Hyungcheol Shin <sup>1,2</sup> <sup>1</sup> Seoul National University, <sup>2</sup> Integra Semiconductor Co., Ltd.
FG3-K-4 16:40-16:55	Simulation Study on the Electrical Characteristics of 3D NAND String with a Locally Deformed Memory Cell Geon-Tae Jang and Sung-Min Hong School of Electrical Engineering and Computer Science, GIST
FG3-K-5 16:55-17:10	Program Strategy of 3D NAND Flash to Mitigate Threshold Voltage Distribution Widening at Cross-Temperature Jiyoon Kim, Chanyang Park, Kihoon Nam, Donghyun Kim, Hyunseo You, and Rock-Hyun Baek Department of Electrical Engineering, POSTECH
FG3-K-6 17:10-17:25	Impacts of Hydrogen Profile on The Reliability Characteristics of Flash Memory Using SiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> /SiO <sub>2</sub> Stack Film by Post Annealing Sehyeon Choi <sup>1</sup> , Sejin Kim <sup>1</sup> , San Park <sup>1</sup> , Boncheol Ku <sup>1</sup> , Hanmei Choi <sup>2</sup> , Hyungjun Kim <sup>2</sup> , Jaehyun Yang <sup>2</sup> , and Changhwan Choi <sup>1</sup> <sup>1</sup> Division of Materials Science & Engineering, Hanyang University, <sup>2</sup> Memory Process Development Team, Samsung Electronics Co., Ltd.